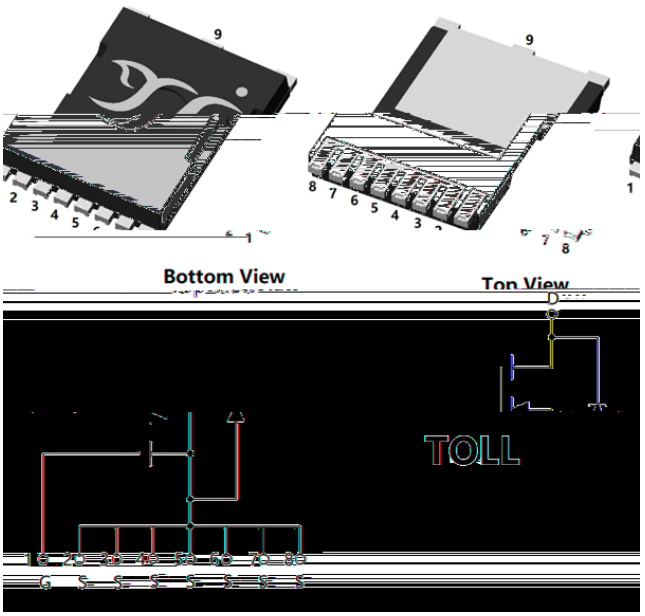
N-Channel Enhancement Mode Field Effect Transistor



Product Summary

V_{DS}	100V
I_D	265A
$R_{DS(ON)}$(at V_{GS}=10V)	2.1m
100% EAS Tested	
100% V_{DS} Tested	

General Description

Split gate trench MOSFET technology
Excellent package for heat dissipation
High density cell design for low $R_{DS(ON)}$
Moisture Sensitivity Level 1
Epoxy Meets UL 94 V-0 Flammability Rating
Halogen Free

Applications

Load switch
Battery management
Solar

Absolute Maximum Ratings (T_J=25 unless otherwise noted)

Parameter			Symbol	Limit	Unit
Drain-source Voltage			V_{DS}	100	V
Gate-source Voltage			V_{GS}	±20	V
Continuous Drain Current (Note 1,2)	Steady-State	T_A=25℃	I_D	25	A
		T_A=100℃		17	
Continuous Drain Current (Note 1,3)	Steady-State	T_C=25℃		265	
		T_C =100℃		187	
Pulsed Drain Current	T_C=25 , t_p=100μs		I_{DM}	1060	A
Avalanche energy	V_G=10V, R_G 2mH, IAS=38.5A		EAS	1482	mJ
Total Power Dissipation (Note 1,2)	Steady-State	T_A=25℃	P_D	3.3	W
		T_A=100℃		1.6	
Total Power Dissipation (Note 1,3)	Steady-State	T_C=25℃		375	
		T_C =100℃		187	
Junction and Storage Temperature Range			T_J ,T_{STG}	-55 +175	℃

Thermal resistance

Parameter		Symbol	Typ	Max	Units
Thermal Resistance Junction-to-Ambient (Note 2)	Steady-State	R	35	45	℃/W
Thermal Resistance Junction-to-Case	Steady-State	R	0.3	0.4	

Ordering Information (Example)

PREFERED P/N	PACKING CODE	Marking	MINIMUM PACKAGE(pcs)	INNER BOX QUANTITY(pcs)	OUTER CARTON QUANTITY(pcs)	DELIVERY MODE
YJT2D1G10H	F1	YJT2D1G10H	2000	4000	20000	13 reel

Electrical Characteristics (T_J=25 unless otherwise noted)

Parameter	Symbol	Conditions	Min	Typ	Max	Units
Static Parameter						
Drain-Source Breakdown Voltage	BV_{DSS}	V_{GS}= 0V, I_D=250	100	-	-	V
		V_{GS}= 0V, I_D=1mA	100	-	-	V
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS}=100V, V_{GS}=0V	-	-	1	
		V_{DS}=100V, V_{GS}=0V, Tj=125℃	-	-	100	
Gate-Body Leakage Current	I_{GSS}	V_{GS}= ±20V, V_{DS}=0V	-	-	±100	nA
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS}= V_{GS}, I_D	2.2	3.0	3.8	V
Static Drain-Source On-Resistance	$R_{DS(ON)}$	V_{GS}=10V, I_D=50A	-	1.5	2.1	
Diode Forward Voltage	V_{SD}	I_S=30A, V_{GS}=0V	-	-	1.2	V
Gate resistance	R_G	f=1MHz	-	0.85	-	
Maximum Body-Diode Continuous Current	I_S		-	-	265	A
Dynamic Parameters						
Input Capacitance	C_{iss}	V_{DS}=50V, V_{GS}=0V, f=1MHz	-	9600	-	pF
Output Capacitance	C_{oss}		-	3245	-	
Reverse Transfer Capacitance	C_{rss}		-	48	-	
Switching Parameters						
Total Gate Charge	Q_g	V_{GS}=10V, V_{DS}=50V, I_D=50A	-	132.5	-	nC
Gate-Source Charge	Q_{gs}		-	55	-	
Gate-Drain Charge	Q_{gd}		-	17	-	
Reverse Recovery Charge	Q_{rr}	I_F=50A, di/dt=100A/us	-	157	-	nC
Reverse Recovery Time	t_{rr}		-	93	-	ns
Turn-on Delay Time	$t_{D(on)}$	V_{GS}=10V, V_{DD}=50V, I_D=50A R_{GEN}=3	-	30	-	ns
Turn-on Rise Time	t_r		-	48	-	
Turn-off Delay Time	$t_{D(off)}$		-	59	-	
Turn-off fall Time	t_f		-	34	-	

Note

1. The entire application environment impacts the thermal resistance values shown, they are not constants and are only valid for the particular conditions noted.
2. The value of R is measured with the device mounted on the 40mm*40mm*1.1mm single layer FR-4 PCB board with 1 in^2 pad of 2oz. Copper, in the still air environment with TA =25 .The maximum allowed junction temperature of 175 . The value in any given application depends on the user's specific board design.
3. Thermal resistance from junction to soldering point (on the exposed drain pad).

■Typical Electrical and Thermal Characteristics Diagrams

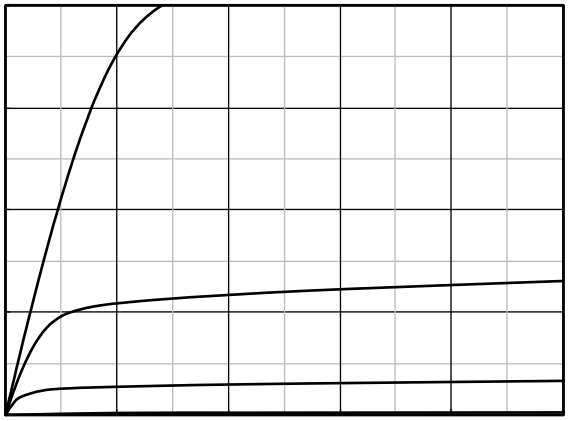


Figure 1. Output Characteristics

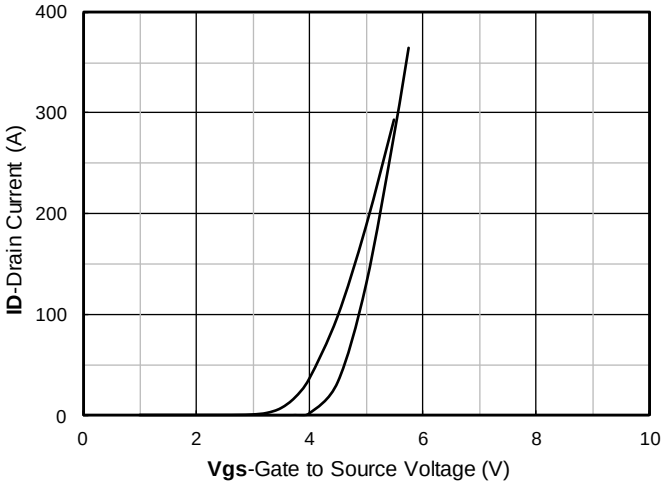


Figure 2. Transfer Characteristics

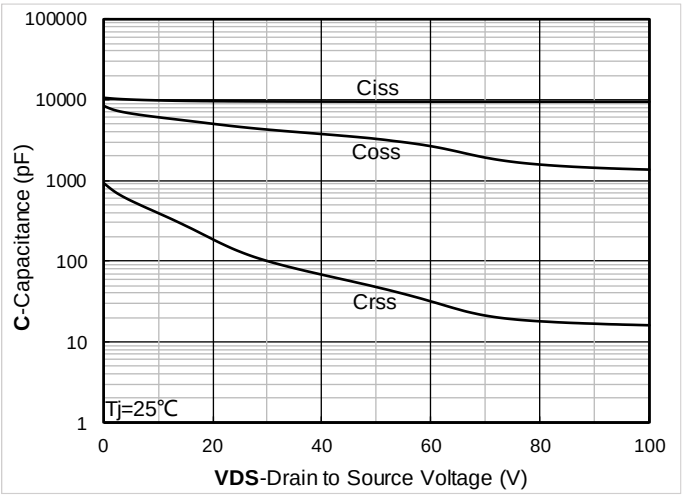


Figure 3. Capacitance Characteristics

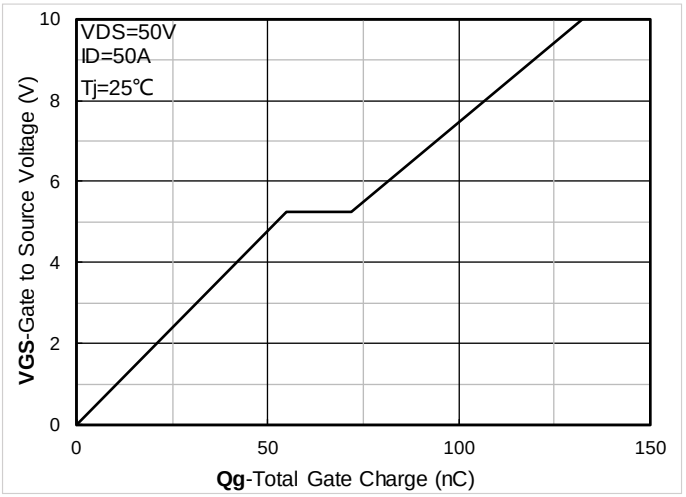


Figure 4. Gate Charge

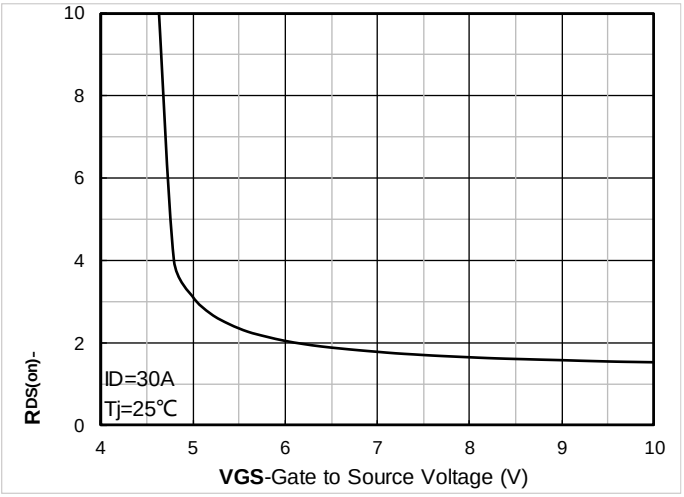


Figure 5. On-Resistance vs Gate to Source Voltage

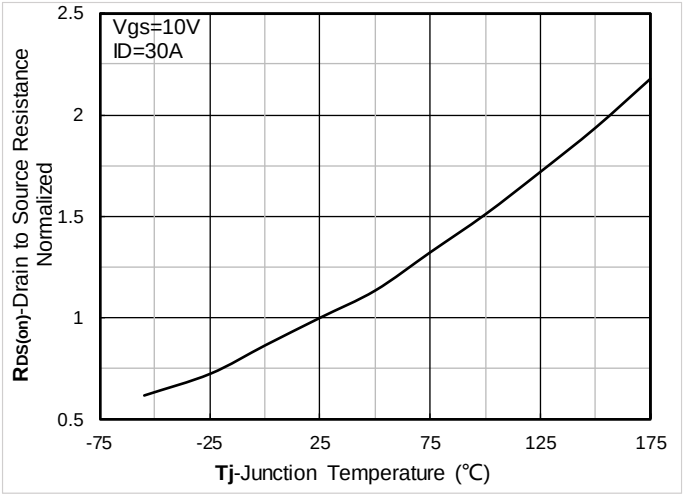


Figure 6. Normalized On-Resistance

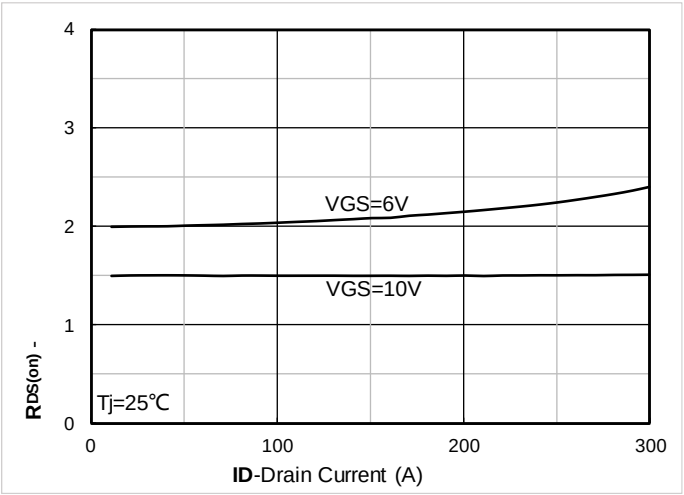


Figure 7. $R_{DS(on)}$ VS Drain Current

Figure 8. Forward characteristics of reverse diode

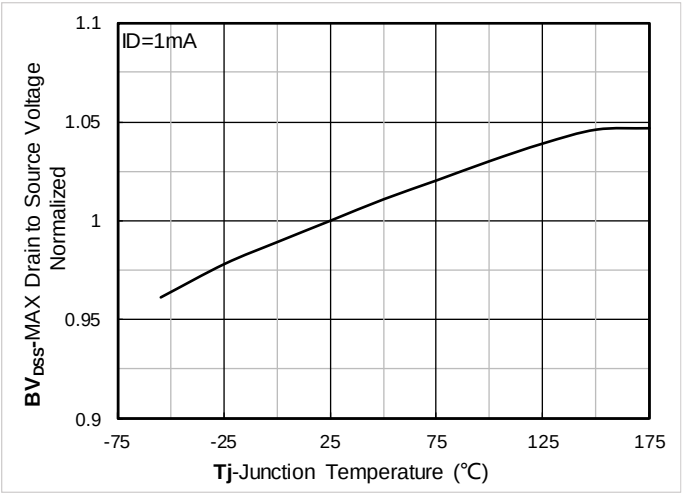


Figure 9. Normalized breakdown voltage

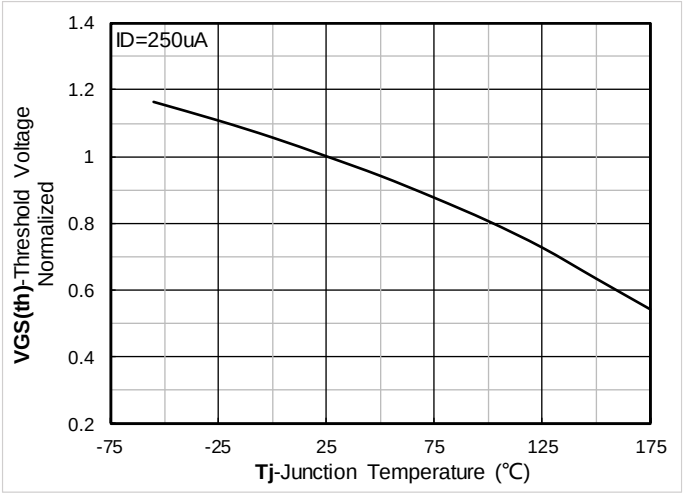


Figure 10. Normalized Threshold voltage

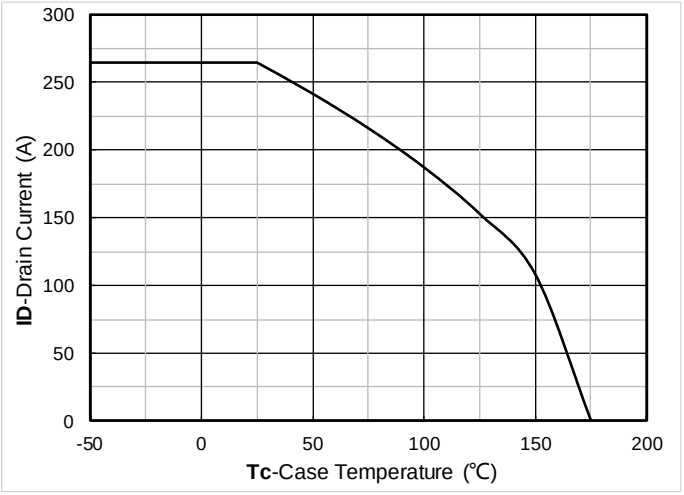


Figure 11. Current dissipation

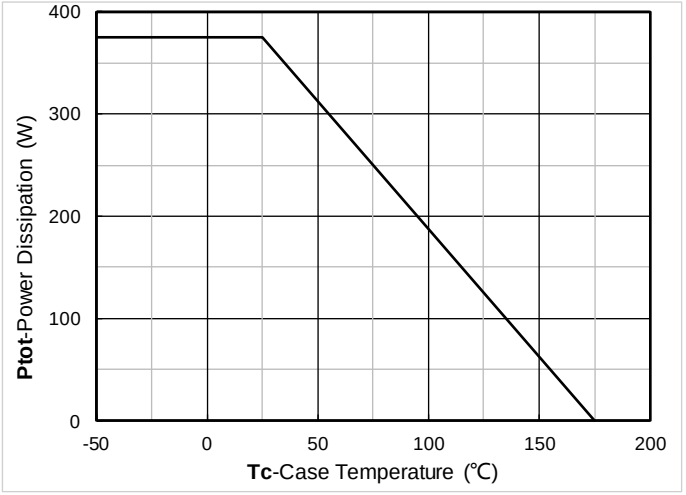


Figure 12. Power dissipation

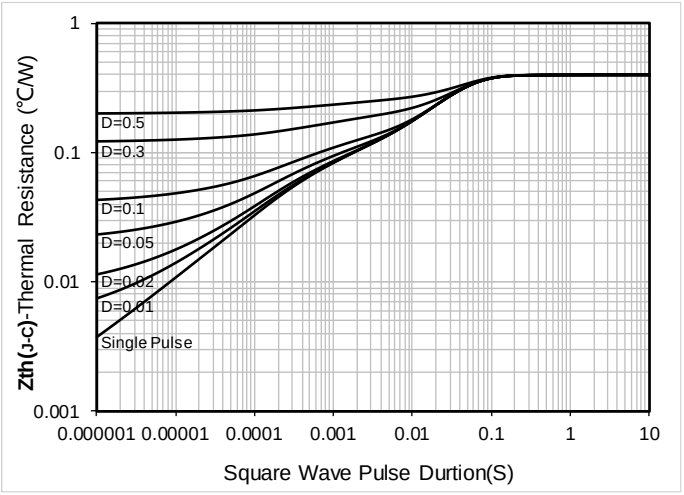


Figure 13. Maximum Transient Thermal Impedance

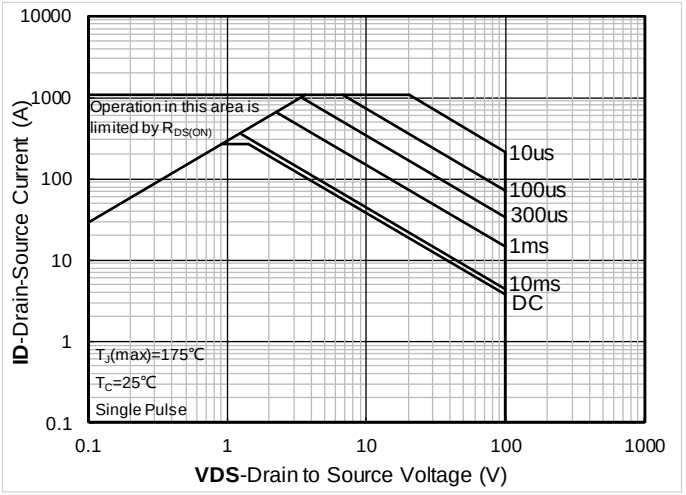


Figure 14. Safe Operation Area

Test Circuits & Waveforms

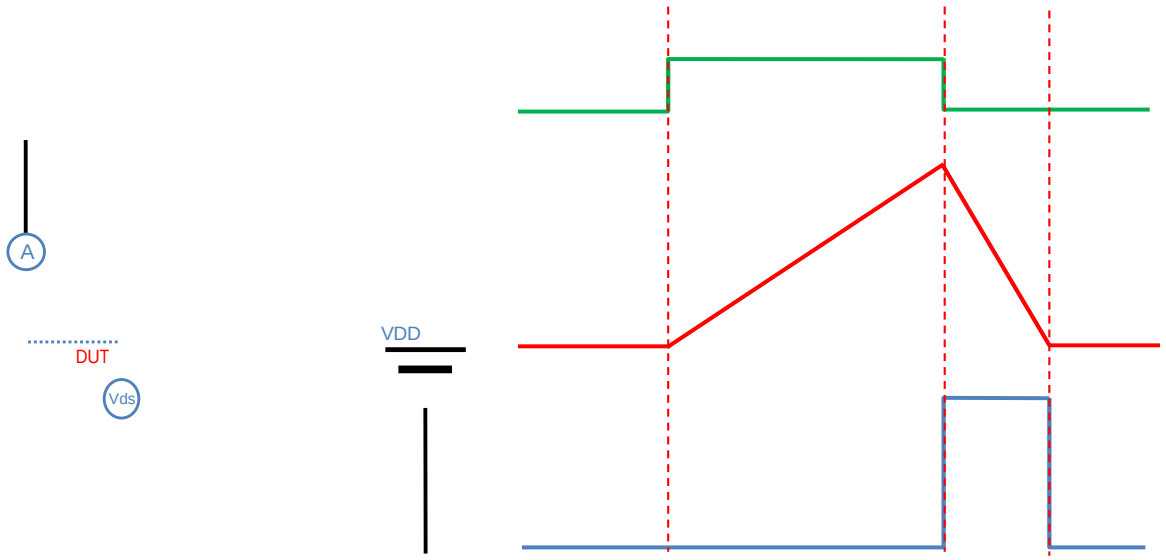


Figure A. Unclamped Inductive Switching (UIS) Test Circuit & Waveform

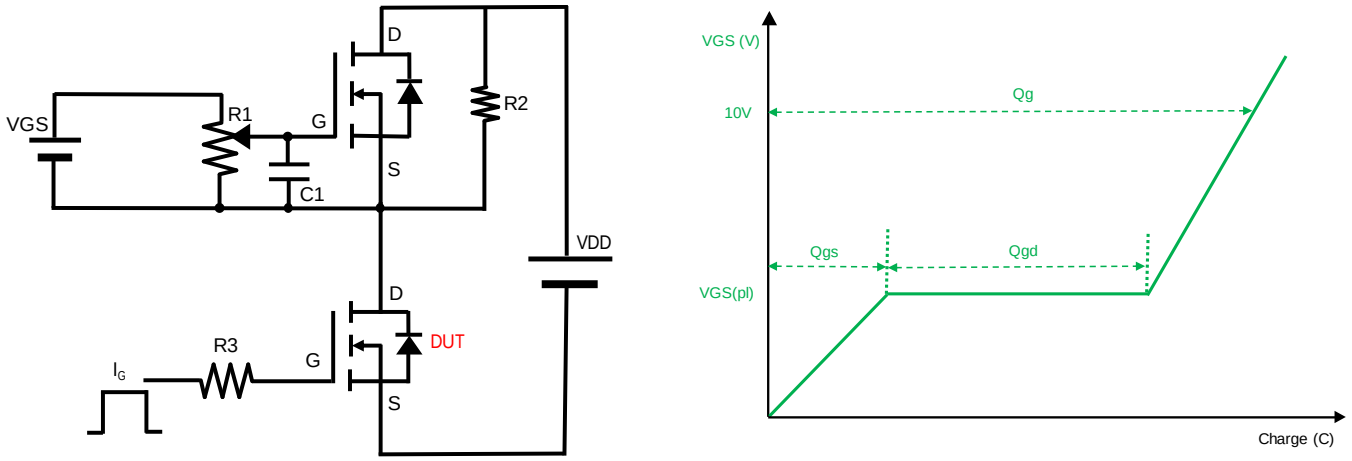


Figure B. Gate Charge Test Circuit & Waveform

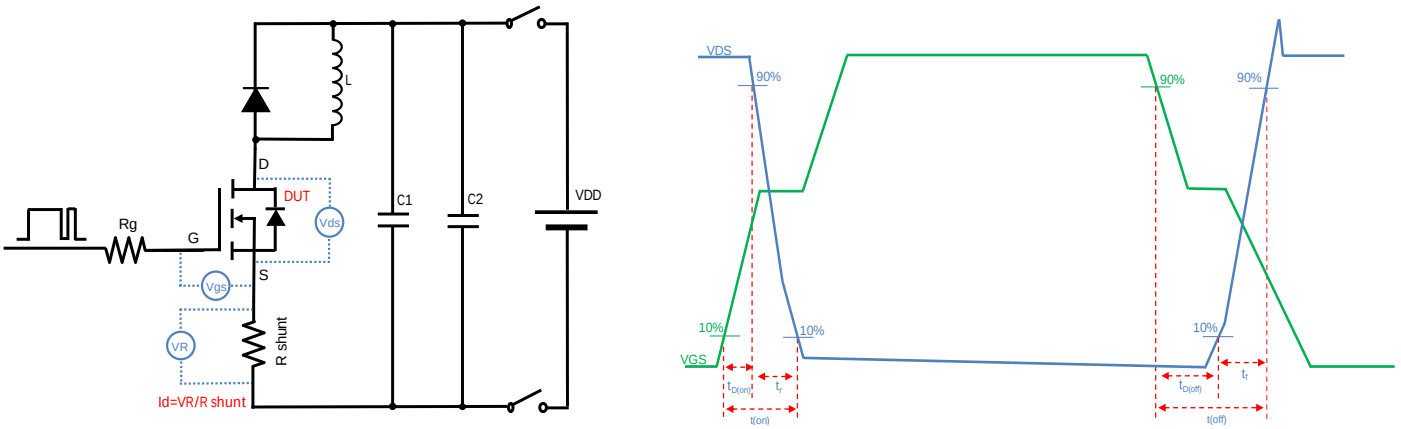


Figure C. Resistive Switching Test Circuit & Waveform

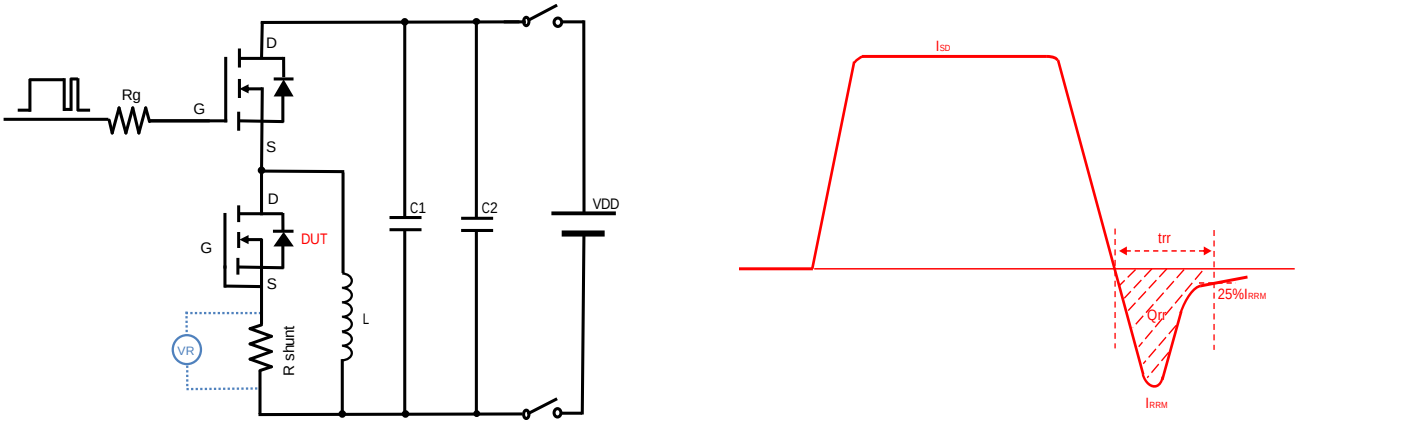
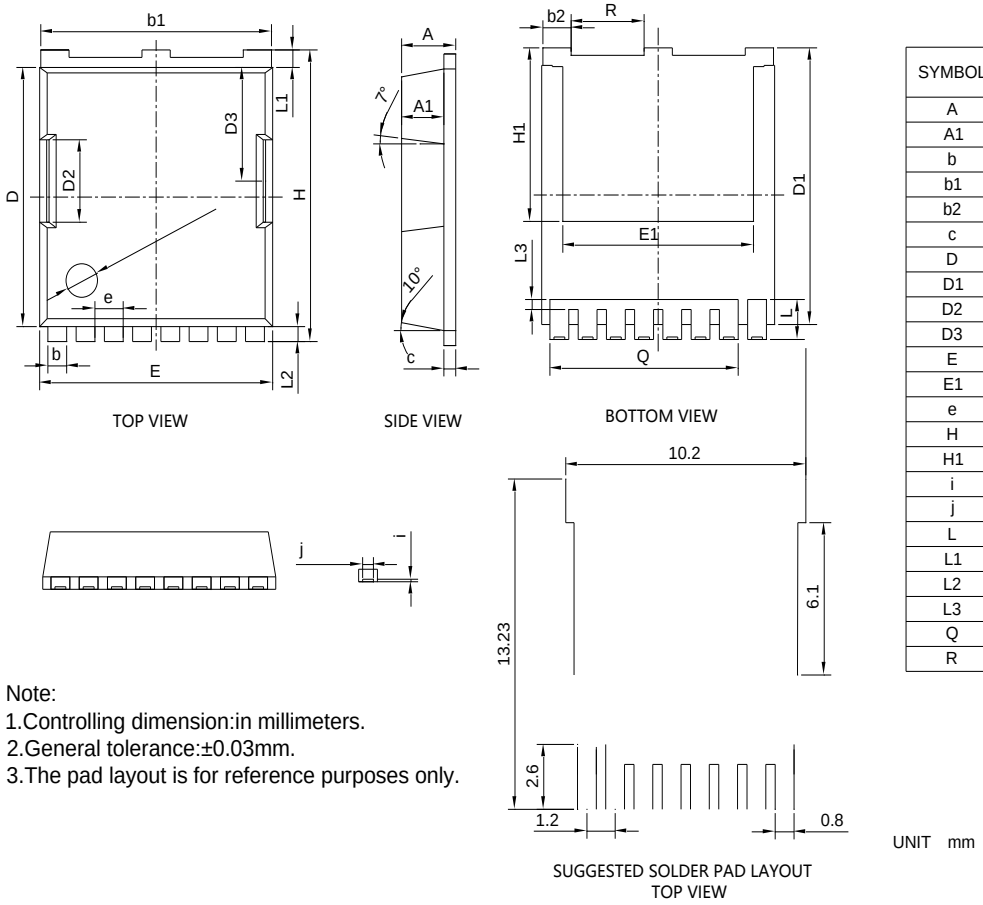


Figure D. Diode Recovery Test Circuit & Waveform

TOLL Package information



SYMBOL	MILLIMETER		
	MIN	NOM	MAX
A	2.2	2.3	2.4
A1	1.7	1.8	1.9
b	0.7	0.8	0.9
b1	9.7	9.8	9.9
b2	1.1	1.2	1.3
c	0.4	0.5	0.6
D	10.28	10.38	10.48
D1	10.98	11.08	11.18
D2	3.2	3.3	3.4
D3	4.45	4.55	4.65
E	9.8	9.9	10
E1	8	8.1	8.2
e		1.2 BSC	
H	11.58	11.68	11.78
H1		6.95 BSC	
i		0.1 REF	
j		0.46 REF	
L	1.5	1.6	1.7
L1	0.6	0.7	0.8
L2	0.5	0.6	0.7
L3	0.3	0.4	0.5
Q		8 REF	
R	3.0	3.1	3.2

Note:
1.Controlling dimension:in millimeters.
2.General tolerance:±0.03mm.
3.The pad layout is for reference purposes only.

UNIT mm